

Claim Status

## Claims 1-13 ( Cancelled)

- 5 14. (Original) A method for forming an emitter, comprising the steps of:  
forming a patterned oxide layer to define an emission area upon an  
electron supply layer; and  
forming a quantum dot zeolite emission layer comprising a plurality of  
cages and having semiconductor materials held within said cages.
- 10 15. (Original) The method of claim 14, further comprising a step of forming a metal  
contact structure on the patterned oxide layer.
- 15 16. (Original) The method of claim 15, further comprising a step of forming a thin  
metal layer on the quantum dot zeolite emission layer and the metal contact  
structure.
- 20 17. (Original) The method of claim 15, wherein the metal contact structure  
comprises a single metal layer.
18. (Original) The method of claim 15, wherein the metal contact structure  
comprises multiple metal layers.
- 25 19. (Original) The method of claim 14, wherein said step of forming an quantum  
dot zeolite emission layer comprises forming a zeolite layer having a thickness in  
the approximate range of 0.05 – 0.5 micrometers.
- 30 20. (Original) The method of claim 14, performed as part of an integrated circuit  
formation process to form the emitter as part of an integrated circuit including  
emitter control circuitry.

## Claims 21-35 (Cancelled)